

C<sup>1</sup>

wherein at least some of the melting of the upper portion of the polycrystalline silicon layer is performed as the amorphous silicon layer is melted.

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C<sup>2</sup>

7. (Twice Amended) A method of forming a polycrystalline silicon layer, comprising:

forming an amorphous silicon layer on a substrate;

melting said amorphous silicon layer using a laser beam so as to form a polycrystalline silicon layer; and

re-melting only an upper portion of said polycrystalline silicon layer using a laser beam so as to re-crystallize said upper portion,

wherein at least some of said re-melting of said upper portion of said polycrystalline silicon layer is performed as said amorphous silicon layer is melted.

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C<sup>3</sup>

18. (Amended) A method of forming a polycrystalline silicon layer, comprising:

forming an amorphous silicon layer on a substrate;

melting the amorphous silicon layer using a laser beam thereby forming the polycrystalline silicon layer using a mask; and

melting only an upper portion of the polycrystalline silicon layer using the laser beam with the mask thereby recrystallizing the upper portion of the polycrystalline silicon layer,